

# 74LVC1G332

Single 3-input OR gate

Rev. 01 — 11 October 2006

Product data sheet

## 1. General description

The 74LVC1G332 is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in mixed 3.3 V and 5 V applications.

Schmitt trigger action at all inputs makes the circuit tolerant of slower input rise and fall time.

This device is fully specified for partial power-down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC1G332 provides one 3-input OR function.

## 2. Features

- Wide supply voltage range from 1.65 V to 5.5 V
- High noise immunity
- Complies with JEDEC standard:
  - ◆ JESD8-7 (1.65 V to 1.95 V)
  - ◆ JESD8-5 (2.3 V to 2.7 V)
  - ◆ JESD8B/JESD36 (2.7 V to 3.6 V)
- $\pm 24$  mA output drive ( $V_{CC} = 3.0$  V)
- CMOS low power consumption
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- ESD protection:
  - ◆ HBM JESD22-A114-D exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
  - ◆ CDM JESD22-C101-C exceeds 1000 V
- Multiple package options
- Specified from  $-40$  °C to  $+85$  °C and  $-40$  °C to  $+125$  °C

### 3. Ordering information

**Table 1. Ordering information**

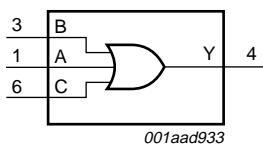
Type number	Package	Temperature range	Name	Description	Version
74LVC1G332GW	SC-88	-40 °C to +125 °C		plastic surface-mounted package; 6 leads	SOT363
74LVC1G332GV	SC-74	-40 °C to +125 °C		plastic surface-mounted package (TSOP6); 6 leads	SOT457
74LVC1G332GM	XSON6	-40 °C to +125 °C		plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1.45 × 0.5 mm	SOT886
74LVC1G332GF	XSON6	-40 °C to +125 °C		plastic extremely thin small outline package; no leads; 6 terminals; body 1 × 1 × 0.5 mm	SOT891

### 4. Marking

**Table 2. Marking**

Type number	Marking code
74LVC1G332GW	YG
74LVC1G332GV	YG
74LVC1G332GM	YG
74LVC1G332GF	YG

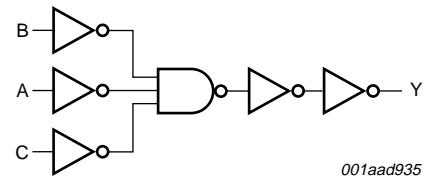
### 5. Functional diagram



**Fig 1. Logic symbol**



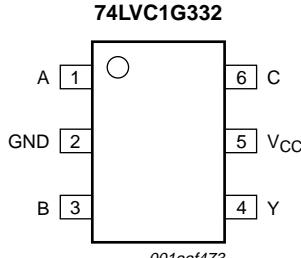
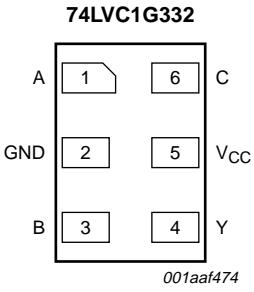
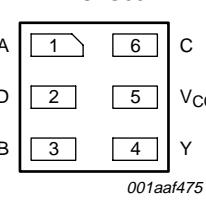
**Fig 2. IEC logic symbol**



**Fig 3. Logic diagram**

## 6. Pinning information

### 6.1 Pinning

 <p><b>Fig 4.</b> Pin configuration SOT363 (SC-88) and SOT457 (SC-74)</p>	 <p><b>Fig 5.</b> Pin configuration SOT886 (XSON6)</p>	 <p><b>Fig 6.</b> Pin configuration SOT891 (XSON6)</p>
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### 6.2 Pin description

**Table 3.** Pin description

Symbol	Pin	Description
A	1	data input A
GND	2	ground (0 V)
B	3	data input B
Y	4	data output Y
V <sub>CC</sub>	5	supply voltage
C	6	data input C

## 7. Functional description

**Table 4.** Function table<sup>[1]</sup>

Input			Output
A	B	C	Y
H	X	X	H
X	H	X	H
X	X	H	H
L	L	L	L

[1] H = HIGH voltage level;  
L = LOW voltage level;  
X = don't care.

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit	
V <sub>CC</sub>	supply voltage		-0.5	+6.5	V	
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < 0 V	-	-50	mA	
V <sub>I</sub>	input voltage		[1]	-0.5	+6.5	V
I <sub>OK</sub>	output clamping current	V <sub>O</sub> > V <sub>CC</sub> or V <sub>O</sub> < 0 V	-	±50	mA	
V <sub>O</sub>	output voltage	Active mode	[1][2]	-0.5	V <sub>CC</sub> + 0.5	V
		Power-down mode	[1][2]	-0.5	+6.5	V
I <sub>O</sub>	output current	V <sub>O</sub> = 0 V to V <sub>CC</sub>	-	±50	mA	
I <sub>CC</sub>	supply current		-	100	mA	
I <sub>GND</sub>	ground current		-	-100	mA	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = -40 °C to +125 °C	[3]	-	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C	

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] When V<sub>CC</sub> = 0 V (Power-down mode), the output voltage can be 5.5 V in normal operation.

[3] For SC-88 packages: above 87.5 °C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K.

For XSON6 packages: above 45 °C the value of P<sub>tot</sub> derates linearly with 2.4 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>CC</sub>	supply voltage		1.65	-	5.5	V
V <sub>I</sub>	input voltage		0	-	5.5	V
V <sub>O</sub>	output voltage	Active mode	0	-	V <sub>CC</sub>	V
		V <sub>CC</sub> = 0 V; Power-down mode	0	-	5.5	V
T <sub>amb</sub>	ambient temperature		-40	-	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 1.65 V to 2.7 V	0	-	20	ns/V
		V <sub>CC</sub> = 2.7 V to 5.5 V	0	-	10	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ <sup>[1]</sup>	Max	Unit
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.7 × V <sub>CC</sub>	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	0.3 × V <sub>CC</sub>	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -4 mA; V <sub>CC</sub> = 1.65 V	1.2	-	-	V
		I <sub>O</sub> = -8 mA; V <sub>CC</sub> = 2.3 V	1.9	-	-	V
		I <sub>O</sub> = -12 mA; V <sub>CC</sub> = 2.7 V	2.2	-	-	V
		I <sub>O</sub> = -24 mA; V <sub>CC</sub> = 3.0 V	2.3	-	-	V
		I <sub>O</sub> = -32 mA; V <sub>CC</sub> = 4.5 V	3.8	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 100 μA; V <sub>CC</sub> = 1.65 V to 5.5 V	-	-	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	-	0.45	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 2.3 V	-	-	0.3	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	-	0.4	V
		I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	-	-	0.55	V
		I <sub>O</sub> = 32 mA; V <sub>CC</sub> = 4.5 V	-	-	0.55	V
I <sub>I</sub>	input leakage current	V <sub>CC</sub> = 0 V to 5.5 V; V <sub>I</sub> = 5.5 V or GND	-	±0.1	±5	μA
I <sub>OFF</sub>	power-off leakage current	V <sub>CC</sub> = 0 V; V <sub>I</sub> or V <sub>O</sub> = 5.5 V	-	±0.1	±10	μA
I <sub>CC</sub>	supply current	V <sub>CC</sub> = 1.65 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A	-	0.1	10	μA
ΔI <sub>CC</sub>	additional supply current	per pin; V <sub>CC</sub> = 2.3 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A	-	5	500	μA
C <sub>I</sub>	input capacitance	V <sub>CC</sub> = 3.3 V; V <sub>I</sub> = GND to V <sub>CC</sub>	-	3	-	pF
<b>T<sub>amb</sub> = -40 °C to +125 °C</b>						
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	0.65 × V <sub>CC</sub>	-	-	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.7	-	-	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	2.0	-	-	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	0.7 × V <sub>CC</sub>	-	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 1.65 V to 1.95 V	-	-	0.35 × V <sub>CC</sub>	V
		V <sub>CC</sub> = 2.3 V to 2.7 V	-	-	0.7	V
		V <sub>CC</sub> = 2.7 V to 3.6 V	-	-	0.8	V
		V <sub>CC</sub> = 4.5 V to 5.5 V	-	-	0.3 × V <sub>CC</sub>	V

**Table 7. Static characteristics ...continued**

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ <sup>[1]</sup>	Max	Unit
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = -100 µA; V <sub>CC</sub> = 1.65 V to 5.5 V	V <sub>CC</sub> - 0.1	-	-	V
		I <sub>O</sub> = -4 mA; V <sub>CC</sub> = 1.65 V	0.95	-	-	V
		I <sub>O</sub> = -8 mA; V <sub>CC</sub> = 2.3 V	1.7	-	-	V
		I <sub>O</sub> = -12 mA; V <sub>CC</sub> = 2.7 V	1.9	-	-	V
		I <sub>O</sub> = -24 mA; V <sub>CC</sub> = 3.0 V	2.0	-	-	V
V <sub>OL</sub>	LOW-level output voltage	I <sub>O</sub> = -32 mA; V <sub>CC</sub> = 4.5 V	3.4	-	-	V
		V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>				
		I <sub>O</sub> = 100 µA; V <sub>CC</sub> = 1.65 V to 5.5 V	-	-	0.1	V
		I <sub>O</sub> = 4 mA; V <sub>CC</sub> = 1.65 V	-	-	0.70	V
		I <sub>O</sub> = 8 mA; V <sub>CC</sub> = 2.3 V	-	-	0.45	V
		I <sub>O</sub> = 12 mA; V <sub>CC</sub> = 2.7 V	-	-	0.60	V
I <sub>I</sub>	input leakage current	I <sub>O</sub> = 24 mA; V <sub>CC</sub> = 3.0 V	-	-	0.80	V
		I <sub>O</sub> = 32 mA; V <sub>CC</sub> = 4.5 V	-	-	0.80	V
I <sub>OFF</sub>	power-off leakage current	V <sub>CC</sub> = 0 V; V <sub>I</sub> or V <sub>O</sub> = 5.5 V	-	-	±200	µA
I <sub>CC</sub>	supply current	V <sub>CC</sub> = 1.65 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A	-	-	200	µA
ΔI <sub>CC</sub>	additional supply current	per pin; V <sub>CC</sub> = 2.3 V to 5.5 V; V <sub>I</sub> = V <sub>CC</sub> - 0.6 V; I <sub>O</sub> = 0 A	-	-	5000	µA

[1] All typical values are measured at V<sub>CC</sub> = 3.3 V and T<sub>amb</sub> = 25 °C.

## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
t <sub>pd</sub>	propagation delay	A, B and C to Y; see <a href="#">Figure 7</a>	[2]					
		V <sub>CC</sub> = 1.65 V to 1.95 V	1.5	4.7	17.2	1.5	21.5	ns
		V <sub>CC</sub> = 2.3 V to 2.7 V	1.0	3.0	6.2	1.0	7.8	ns
		V <sub>CC</sub> = 2.7 V	1.0	3.0	6.0	1.0	7.5	ns
		V <sub>CC</sub> = 3.0 V to 3.6 V	1.0	2.6	4.8	1.0	6.2	ns
		V <sub>CC</sub> = 4.5 V to 5.5 V	1.0	1.9	3.5	1.0	4.4	ns

**Table 8. Dynamic characteristics ...continued**Voltages are referenced to GND (ground = 0 V). For test circuit see [Figure 8](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ <sup>[1]</sup>	Max	Min	Max	
C <sub>PD</sub>	power dissipation capacitance	V <sub>I</sub> = GND to V <sub>CC</sub> ; V <sub>CC</sub> = 3.3 V	[3]	-	12	-	-	pF

[1] Typical values are measured at T<sub>amb</sub> = 25 °C and V<sub>CC</sub> = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.[2] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>.[3] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW):

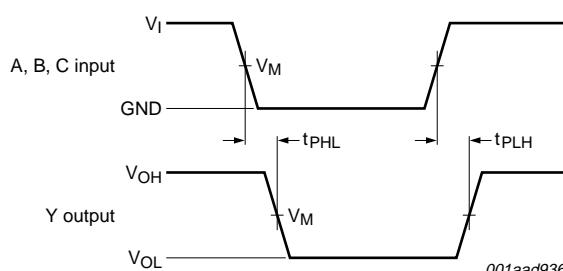
$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum(C_L \times V_{CC}^2 \times f_o)$$

f<sub>i</sub> = input frequency in MHz;f<sub>o</sub> = output frequency in MHz;C<sub>L</sub> = output load capacitance in pF;V<sub>CC</sub> = supply voltage in V;

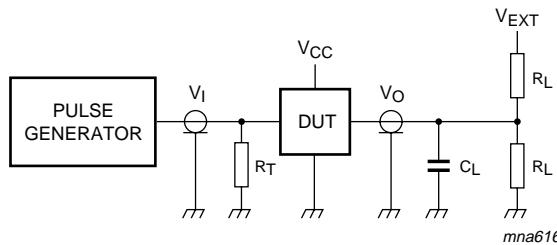
N = number of inputs switching;

 $\sum(C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

## 12. AC waveforms

Measurement points are given in [Table 9](#).V<sub>OL</sub> and V<sub>OH</sub> are typical output voltage drops that occur with the output load.**Fig 7. The input A, B and C to output Y propagation delays****Table 9. Measurement points**

Supply voltage	Input	Output
V <sub>CC</sub>	V <sub>M</sub>	V <sub>M</sub>
1.65 V to 1.95 V	0.5 × V <sub>CC</sub>	0.5 × V <sub>CC</sub>
2.3 V to 2.7 V	0.5 × V <sub>CC</sub>	0.5 × V <sub>CC</sub>
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	0.5 × V <sub>CC</sub>	0.5 × V <sub>CC</sub>



Test data is given in [Table 10](#).

Definitions for test circuit:

$R_L$  = Load resistance.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_T$  = Termination resistance; should be equal to the output impedance  $Z_0$  of the pulse generator.

$V_{EXT}$  = External voltage for measuring switching times.

**Fig 8. Load circuitry for switching times**

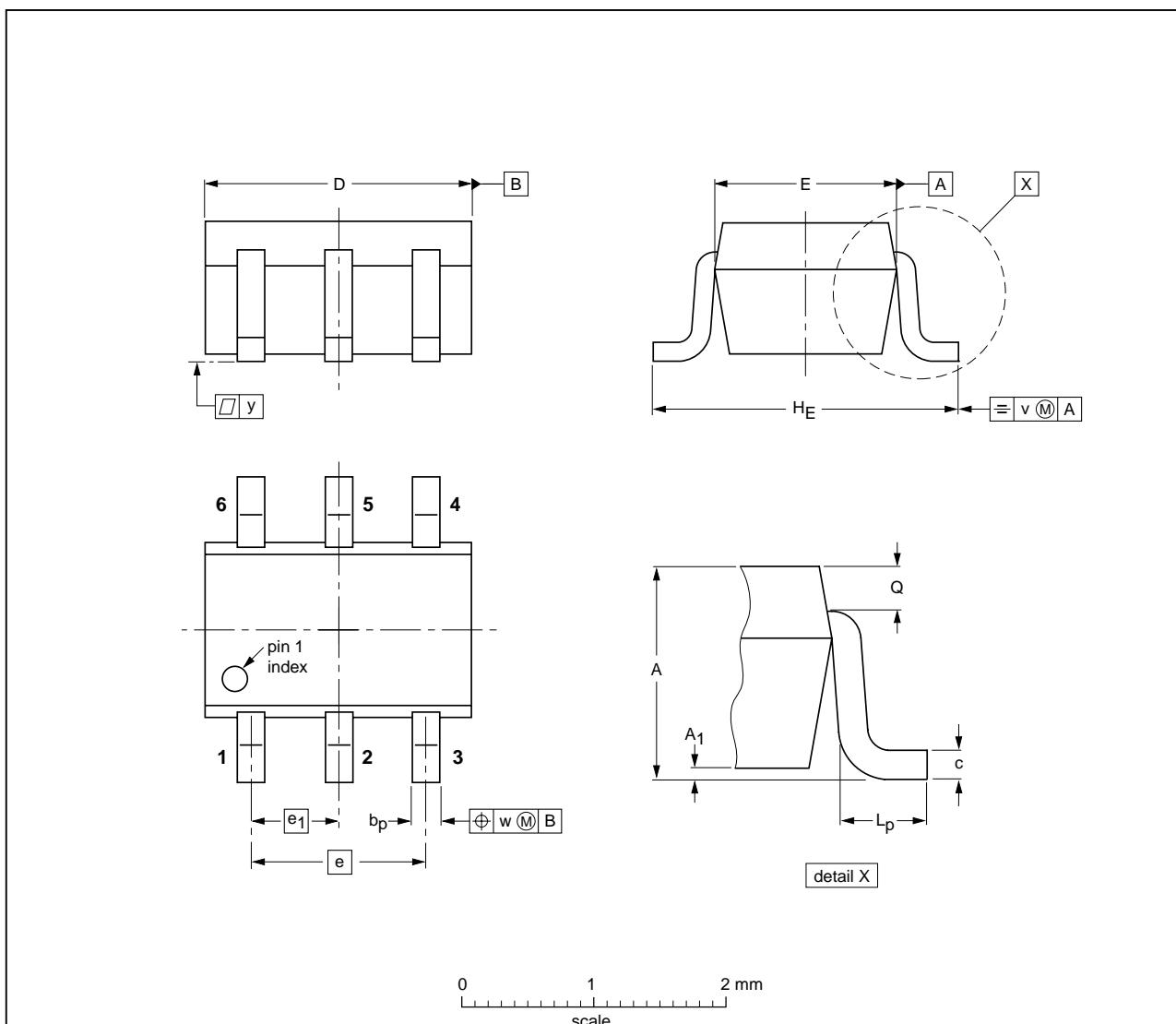
**Table 10. Test data**

Supply voltage	Input		Load		$V_{EXT}$
$V_{CC}$	$V_I$	$t_r = t_f$	$C_L$	$R_L$	$t_{PLH}, t_{PHL}$
1.65 V to 1.95 V	$V_{CC}$	$\leq 2.0$ ns	30 pF	1 k $\Omega$	open
2.3 V to 2.7 V	$V_{CC}$	$\leq 2.0$ ns	30 pF	500 $\Omega$	open
2.7 V	2.7 V	$\leq 2.5$ ns	50 pF	500 $\Omega$	open
3.0 V to 3.6 V	2.7 V	$\leq 2.5$ ns	50 pF	500 $\Omega$	open
4.5 V to 5.5 V	$V_{CC}$	$\leq 2.5$ ns	50 pF	500 $\Omega$	open

## 13. Package outline

Plastic surface-mounted package; 6 leads

SOT363



DIMENSIONS (mm are the original dimensions)

UNIT	A	$A_1$ max	$b_p$	c	D	E	e	$e_1$	$H_E$	$L_p$	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT363			SC-88			-04-11-08- 06-03-16

Fig 9. Package outline SOT363 (SC-88)

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

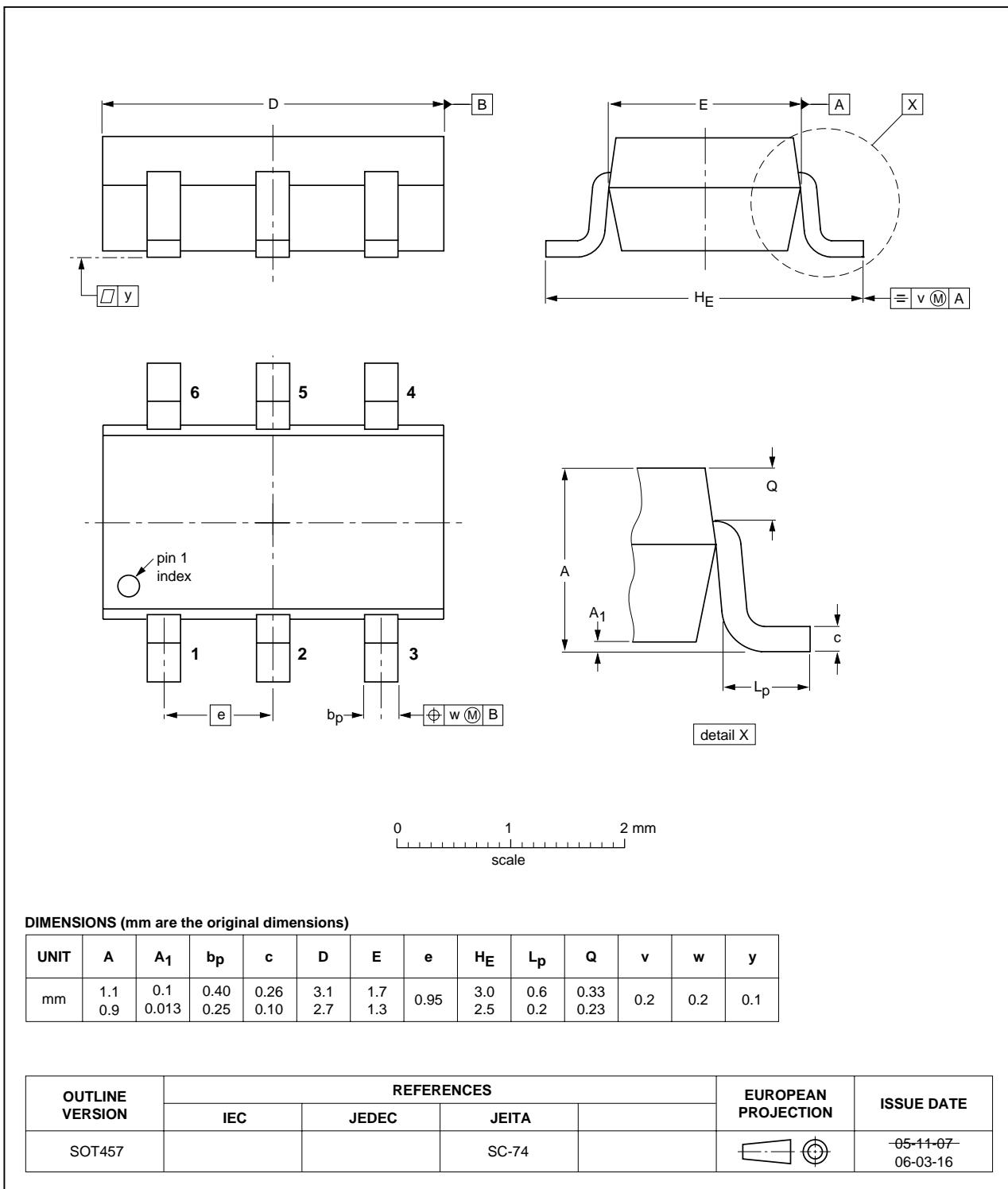


Fig 10. Package outline SOT457 (SC-74)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body  $1 \times 1.45 \times 0.5$  mm

SOT886

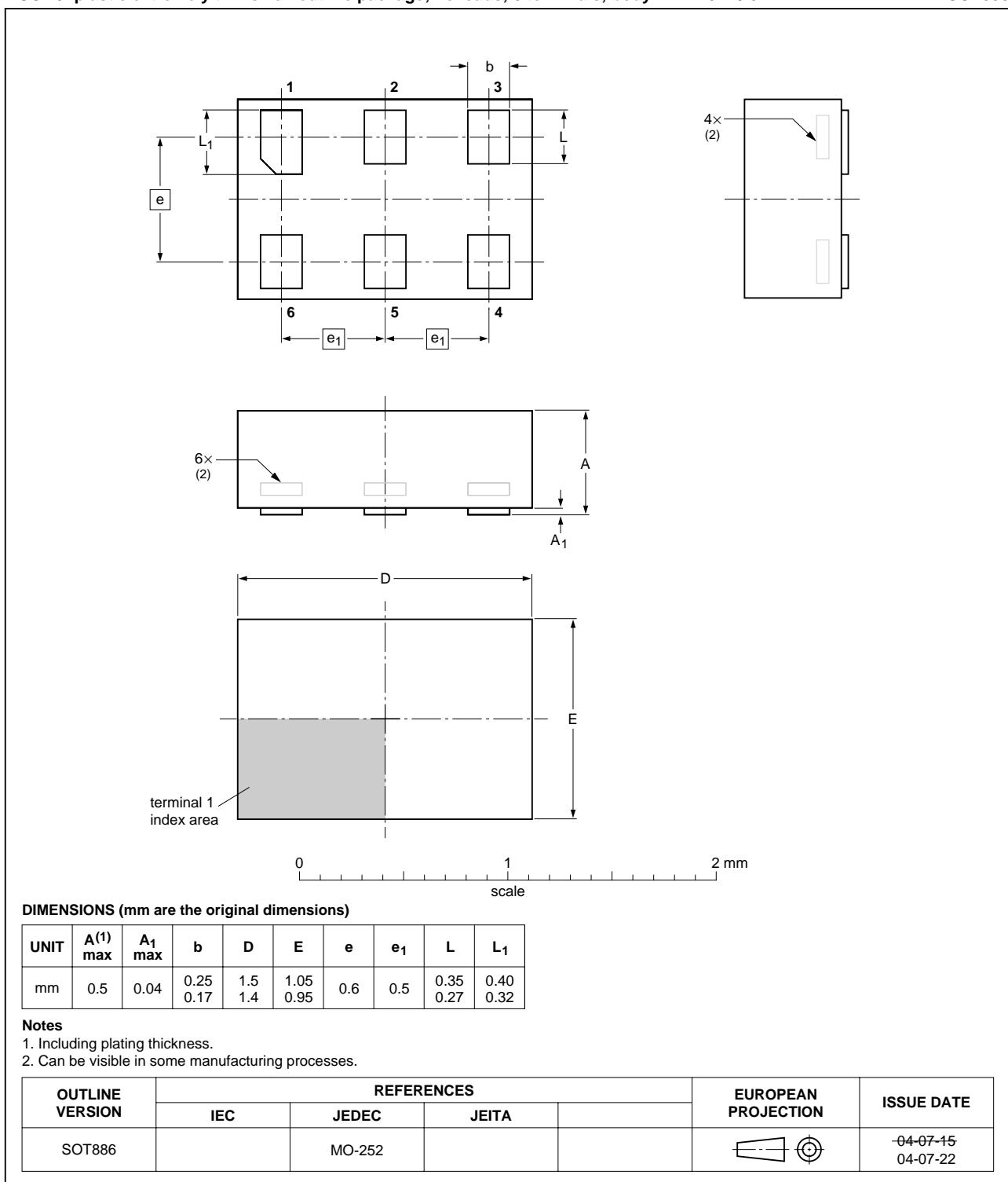
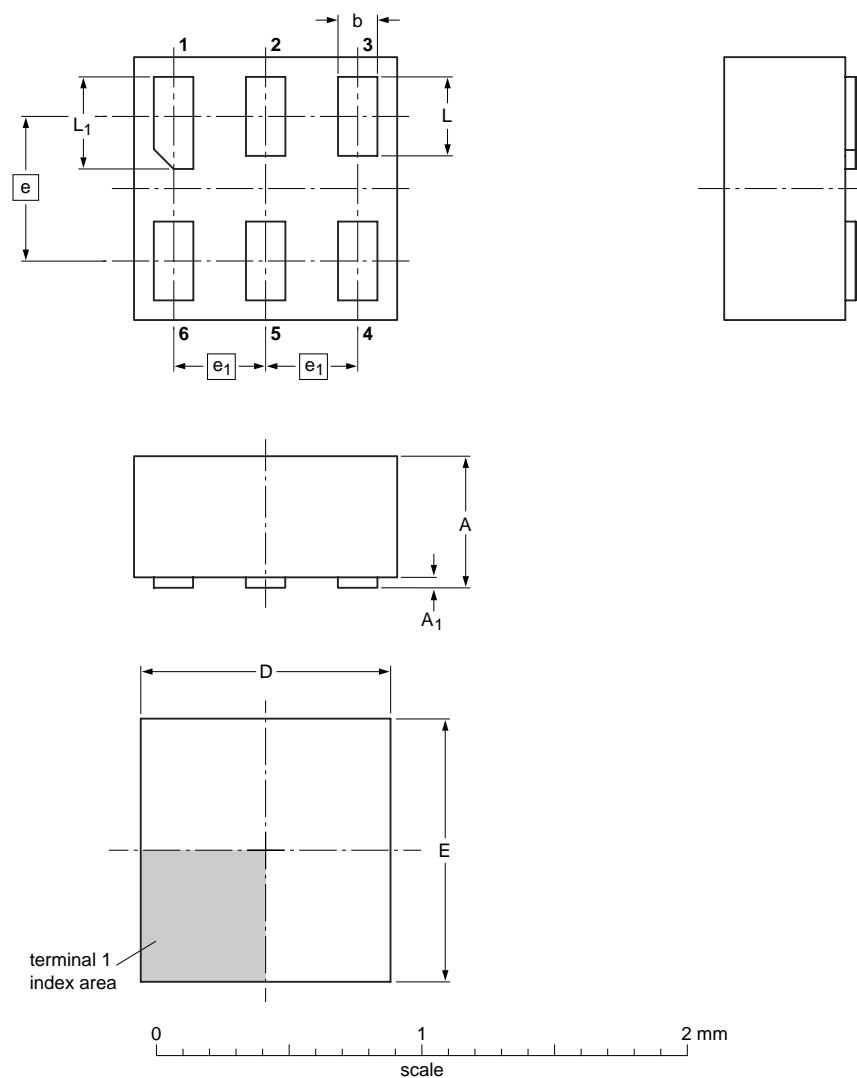


Fig 11. Package outline SOT886 (XSON6)

XSON6: plastic extremely thin small outline package; no leads; 6 terminals; body 1 x 1 x 0.5 mm

SOT891



## DIMENSIONS (mm are the original dimensions)

UNIT	A max	A <sub>1</sub> max	b	D	E	e	e <sub>1</sub>	L	L <sub>1</sub>
mm	0.5	0.04	0.20 0.12	1.05 0.95	1.05 0.95	0.55	0.35	0.35 0.27	0.40 0.32

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT891						-05-03-11 05-04-06

Fig 12. Package outline SOT891 (XSON6)

## 14. Abbreviations

**Table 11. Abbreviations**

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 15. Revision history

**Table 12. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVC1G332_1	20061011	Product data sheet	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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